

THE MEASUREMENT OF RADIATION DAMAGE EFFECTS IN CCD

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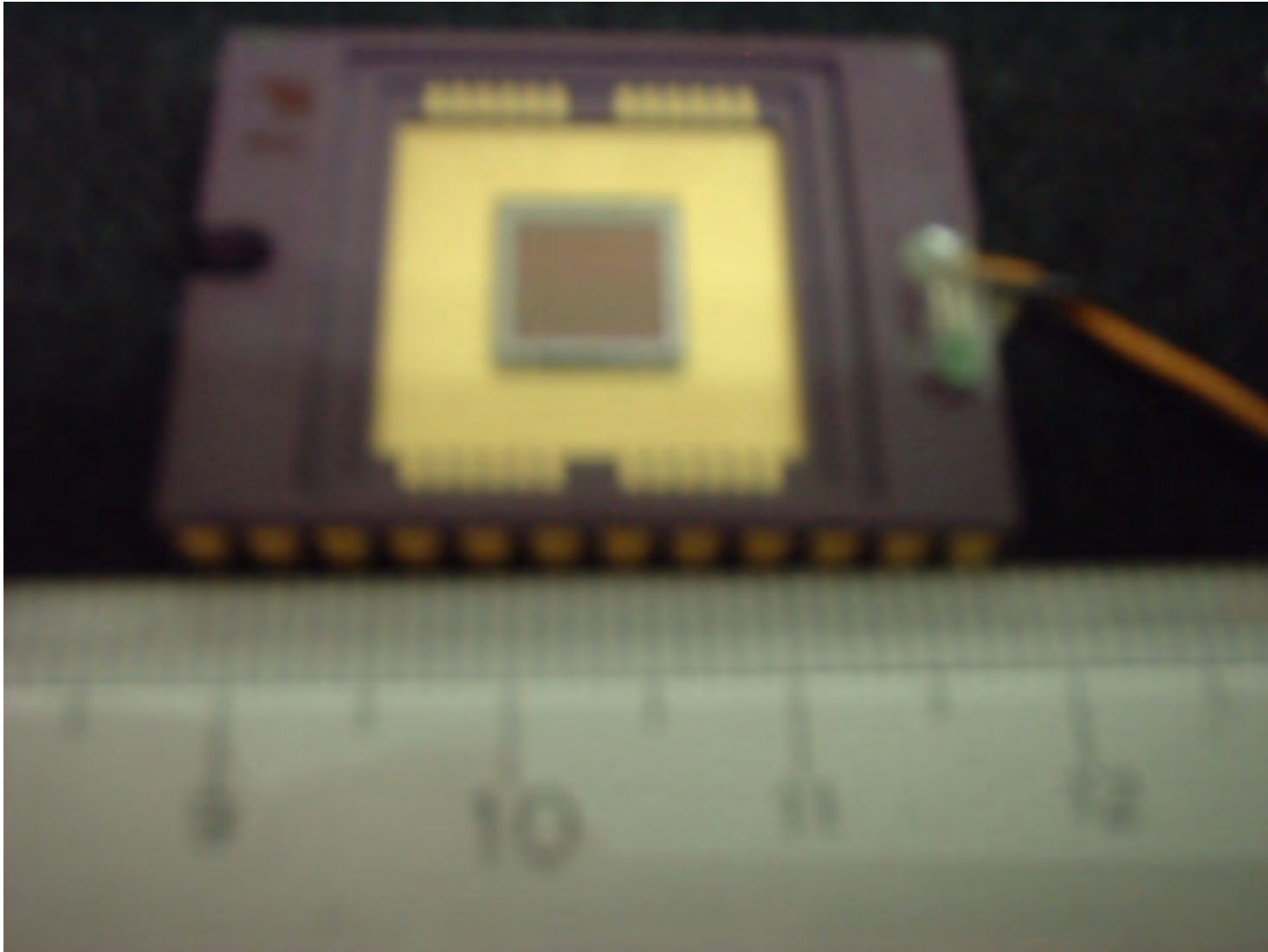
OUTLINE

- Introduction
- CCD overview
- CCD problems
- Experiment
- Analysis
- Summary

INTRODUCTION

- CCD will be use in JLC as vertex detector.
- Requirement from JLC
 - long-range run at $\sim 0^{\circ}\text{C}$
 - radiation hardness, $\sim 4.5 \times 10^{11} e/\text{cm}^2/\text{year}$
 - spacial resolution, \sim several μm
 - fast readout, \sim several $\times 10$ Mpixel/sec

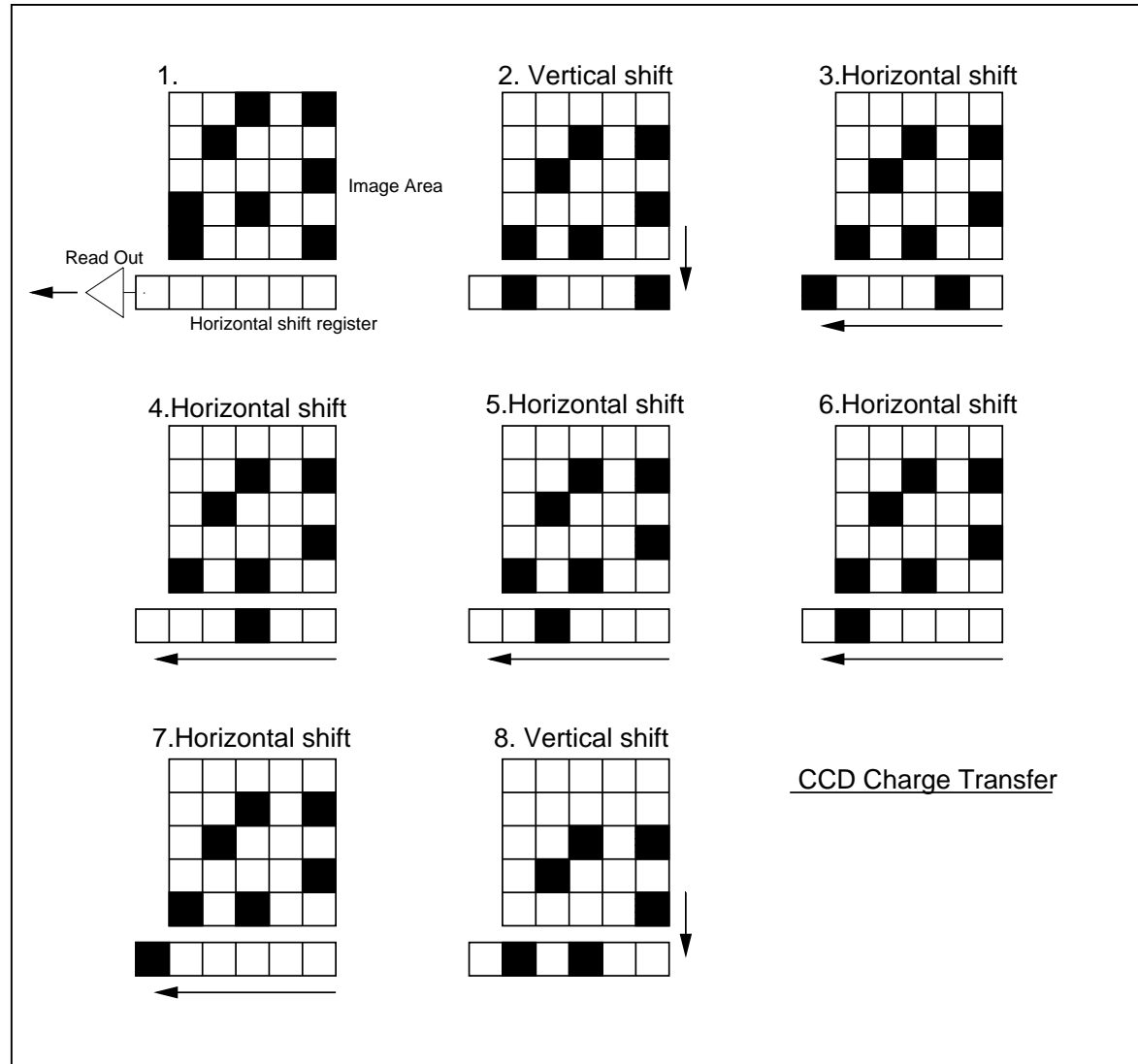
SPEC I



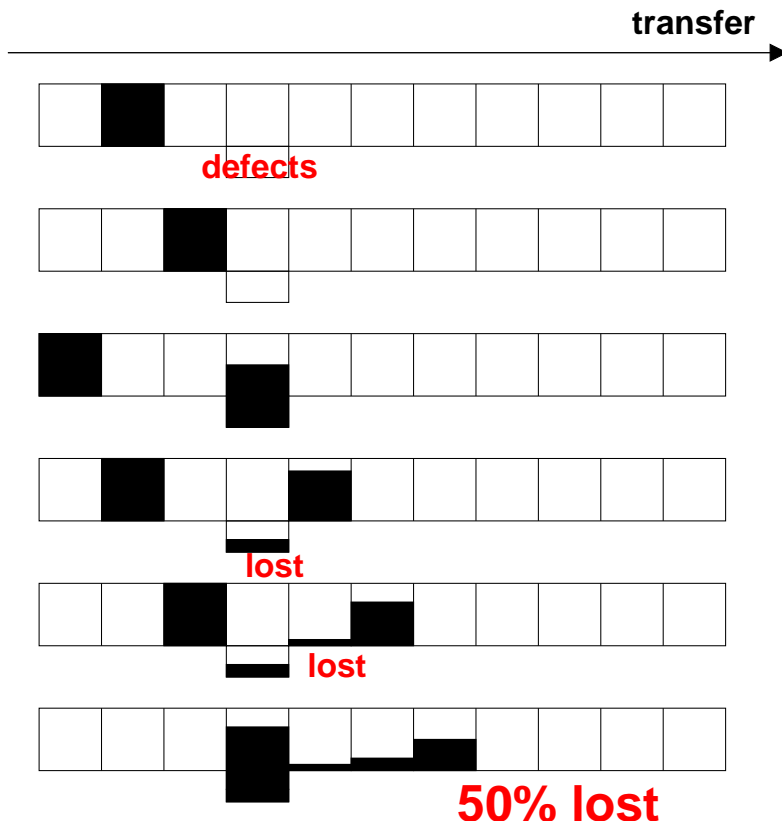
SPEC II

Format	$256(\text{H}) \times 256(\text{V})$
Pixel size	$24\mu\text{m} \times 24\mu\text{m}$
Thickness	$10\mu\text{m}$
Gain	$2\mu\text{V}/e$

CHARGE TRANSFER



CHARGE TRANSFER INEFFICIENCY



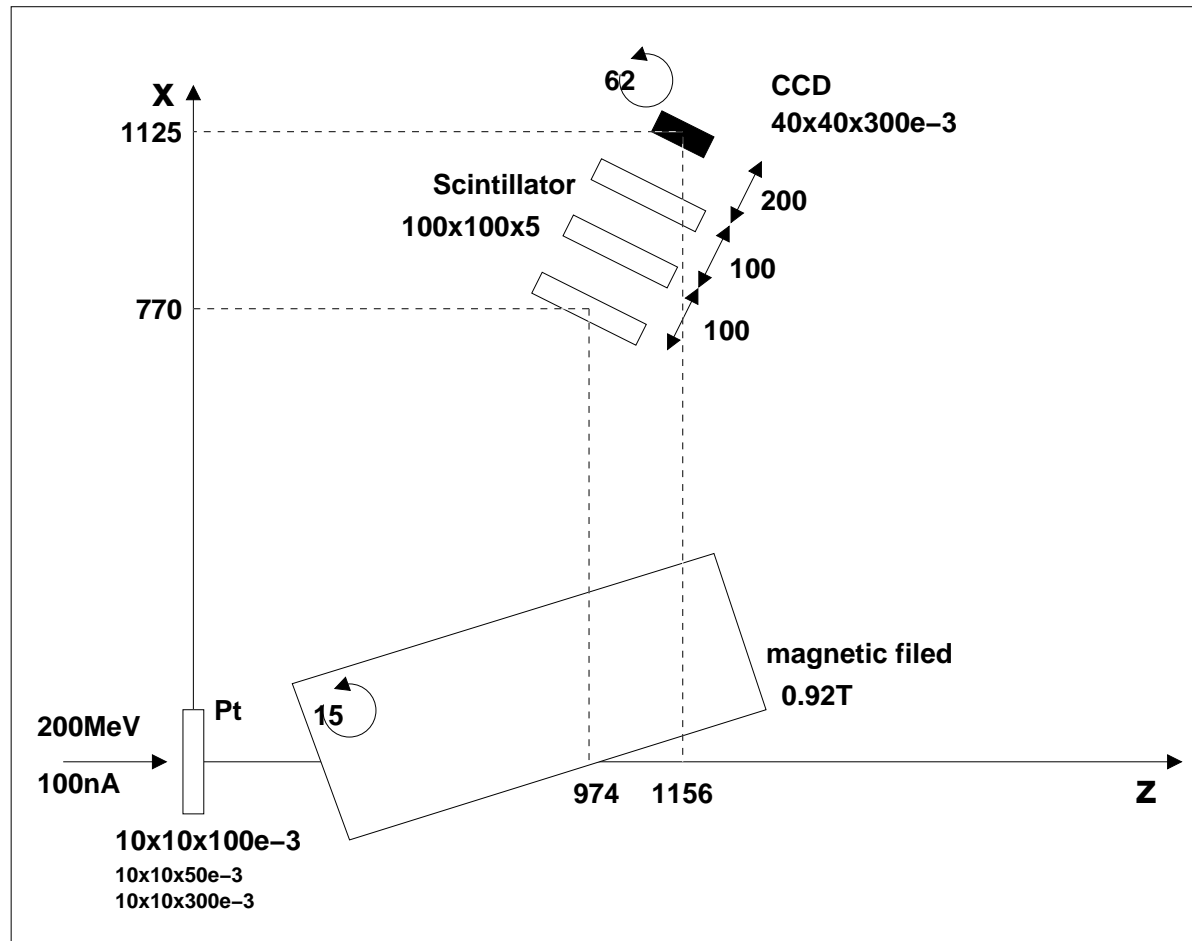
Charge **T**ransfer **E**fficiency is efficiency by a transfer.

$$CTI = 1 - CTE$$

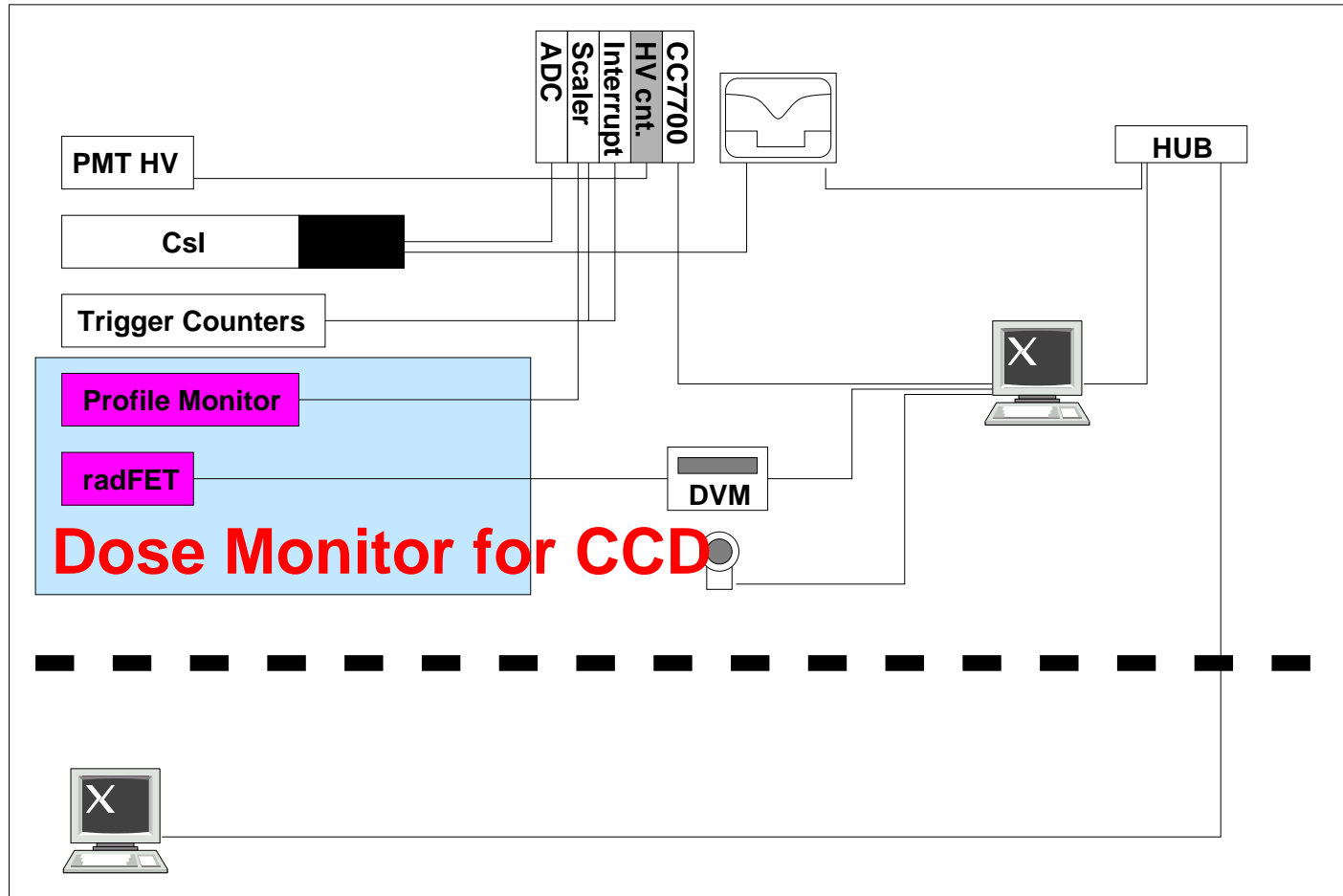
This example, both of CTE and CTI is 0.5.

BEAMTEST I

Dec. 2002, KAKURIKEN, Tohoku University,

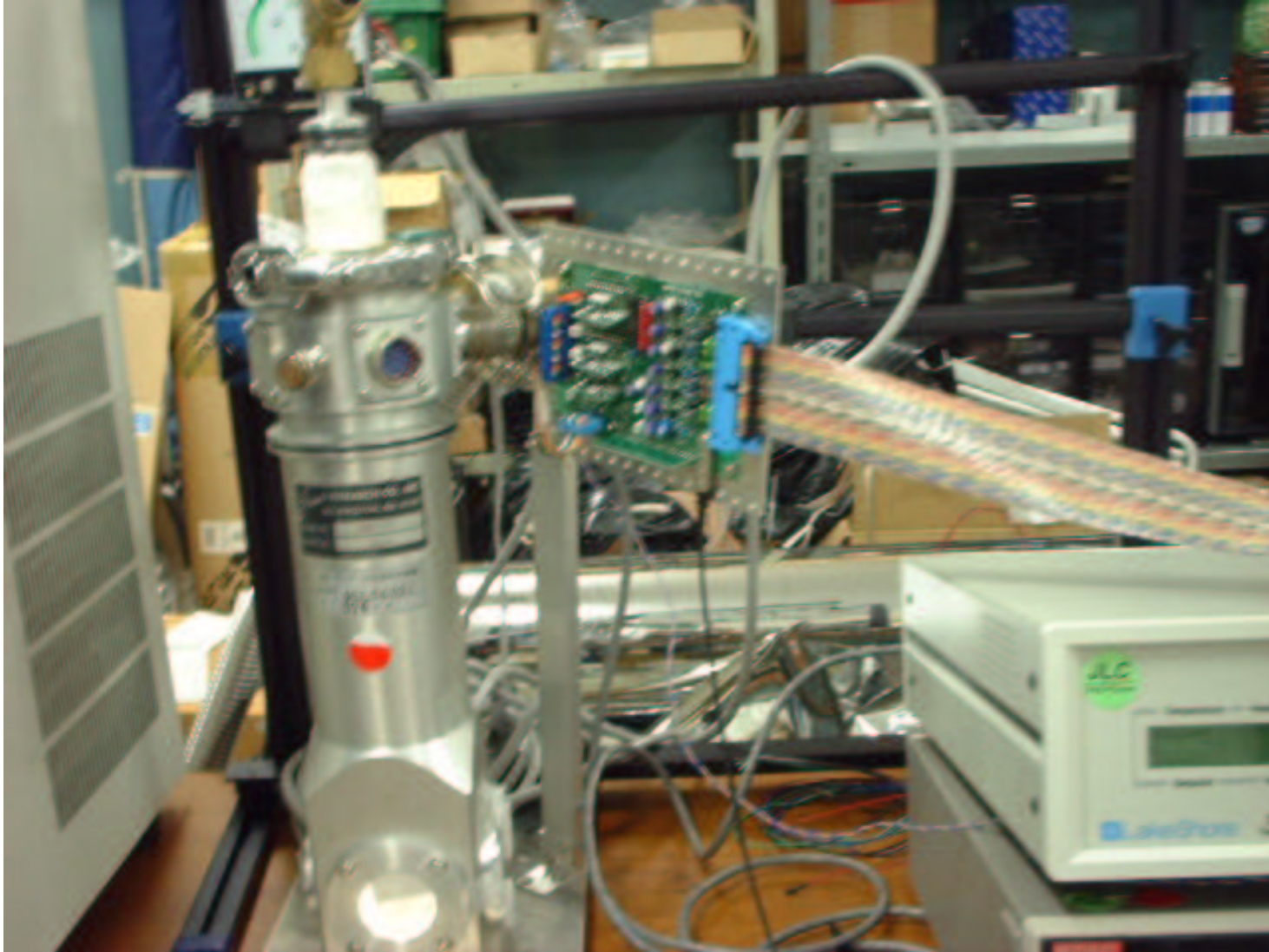


BEAMTEST II

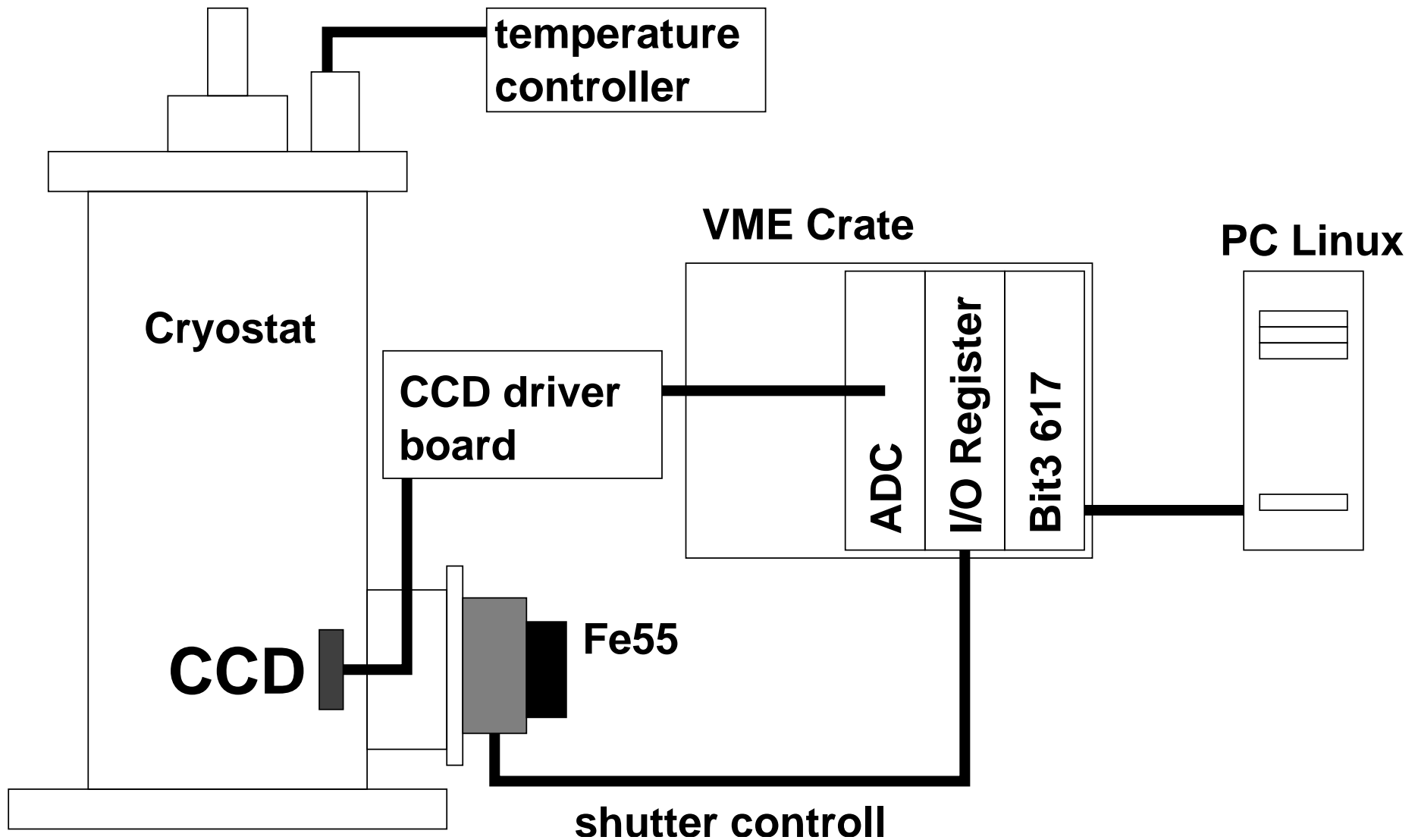


irradiated $\sim 3.6 \times 10^{10} e/cm^2$ (~ 0.95 krad)

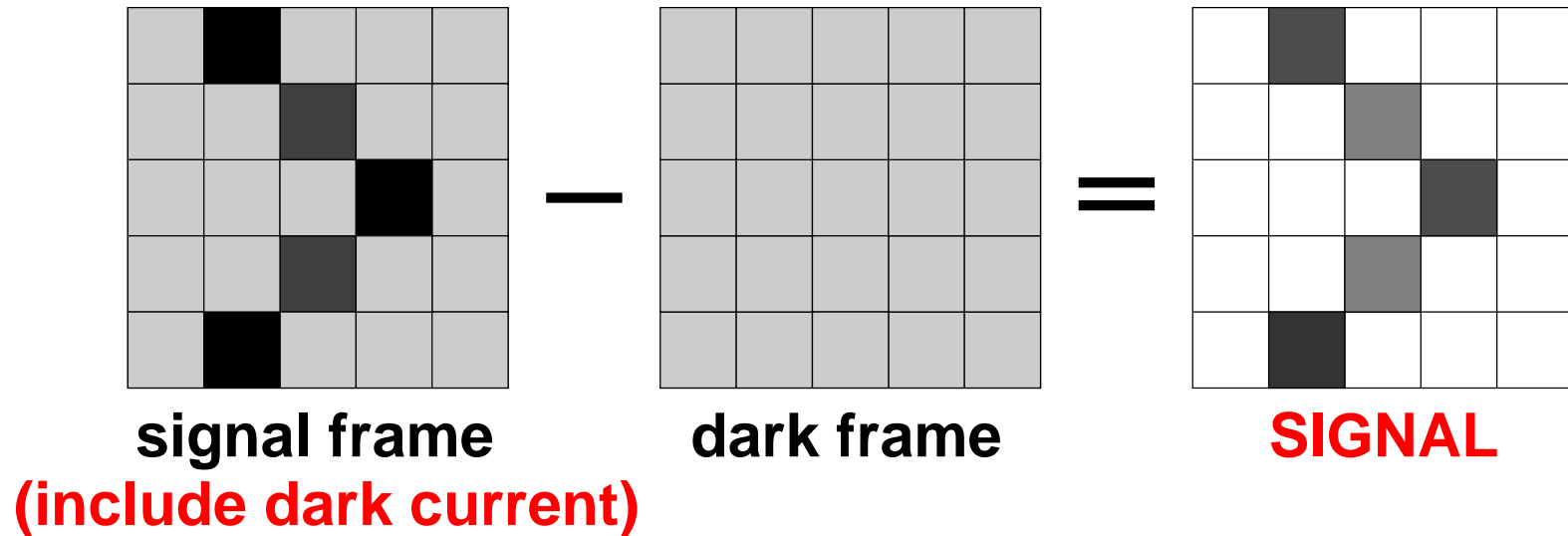
EXPERIMENTAL SETUP I



EXPERIMENTAL SETUP II



SINGLE PIXEL EVENT I



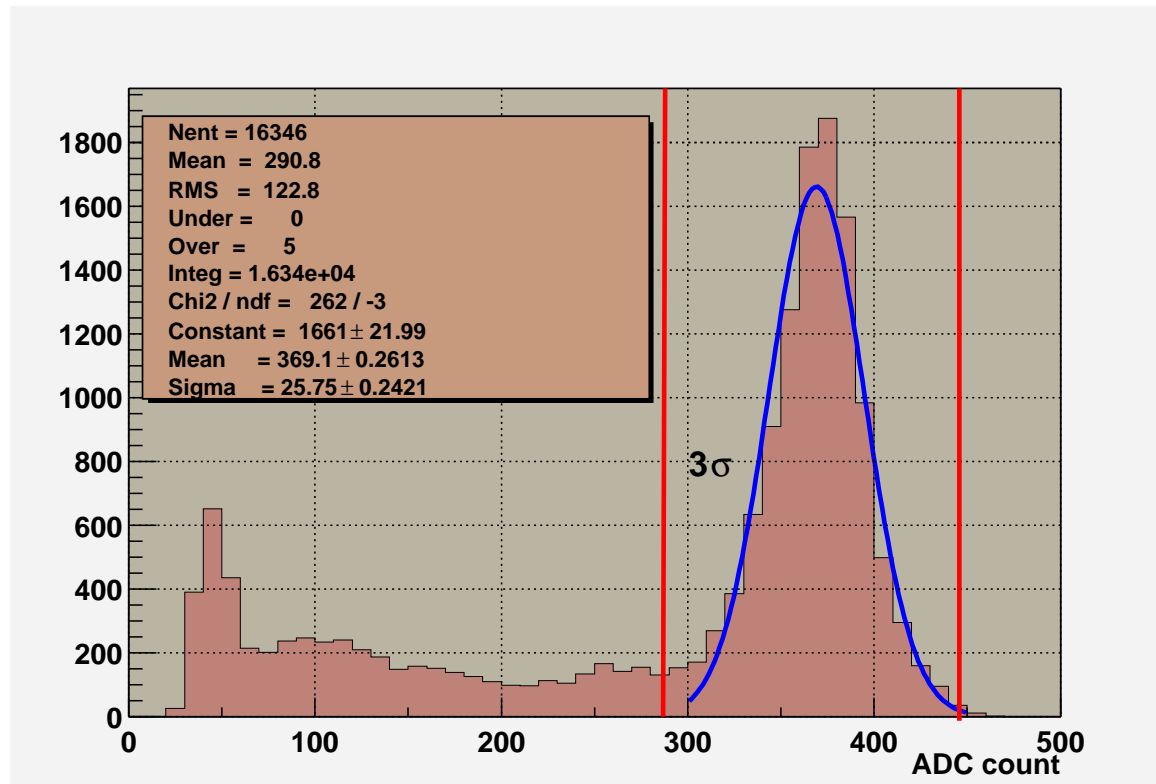
find out single pixel event from signal exclude dark.

SINGLE PIXEL EVENT II

- make a average map of dark current.
- make a RMS map of dark current.
- make a bad channel map.
 - rate of overflow or underflow is more than half.
 - RMS value is more than 20.(this is $\sim 3\sigma$)
- more than average of dark $+6\sigma$.
- no bad channel around.
- not a bad channel.

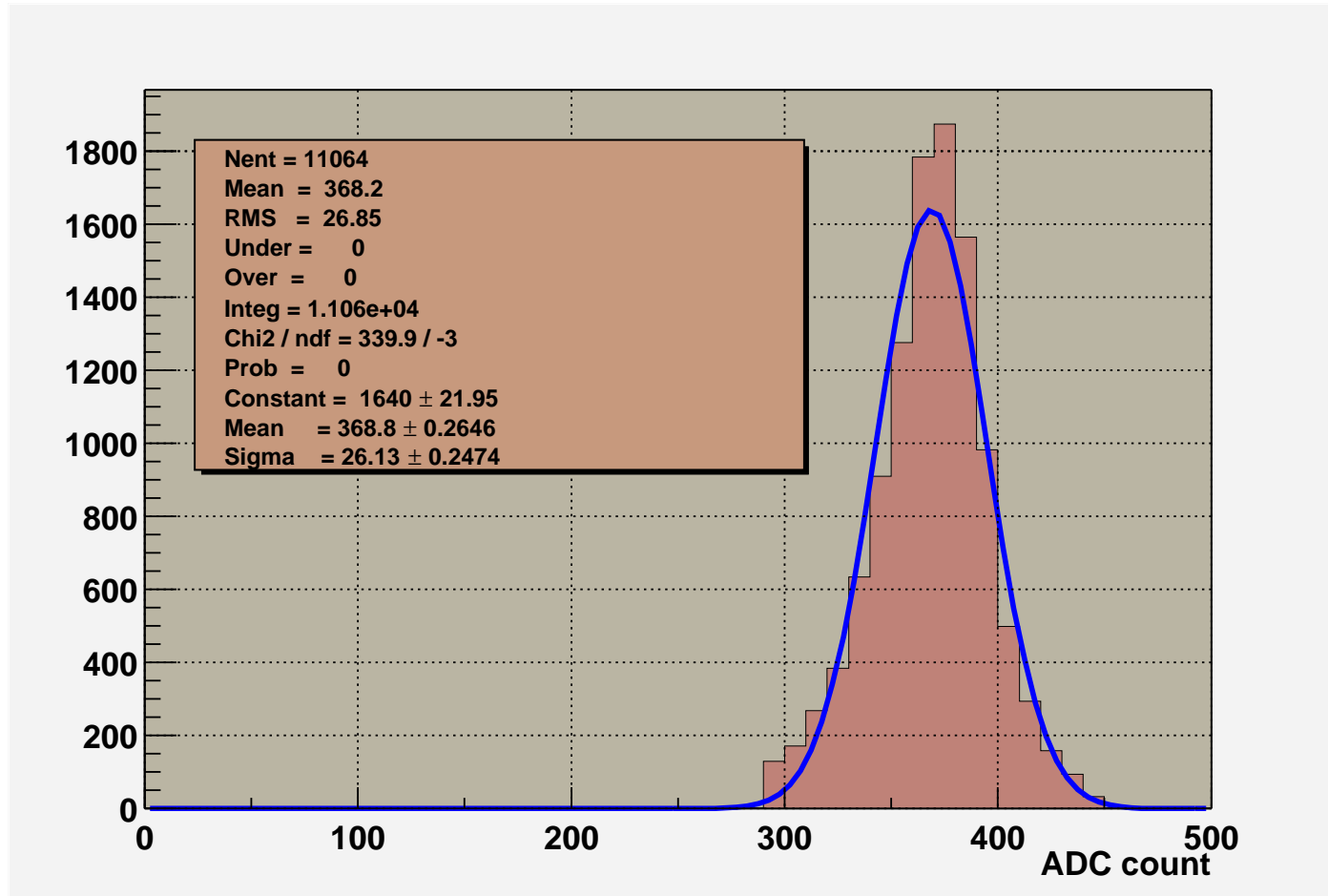
SINGLE PIXEL EVENT III

ex.) CCD before irradiation (@ -80°C)



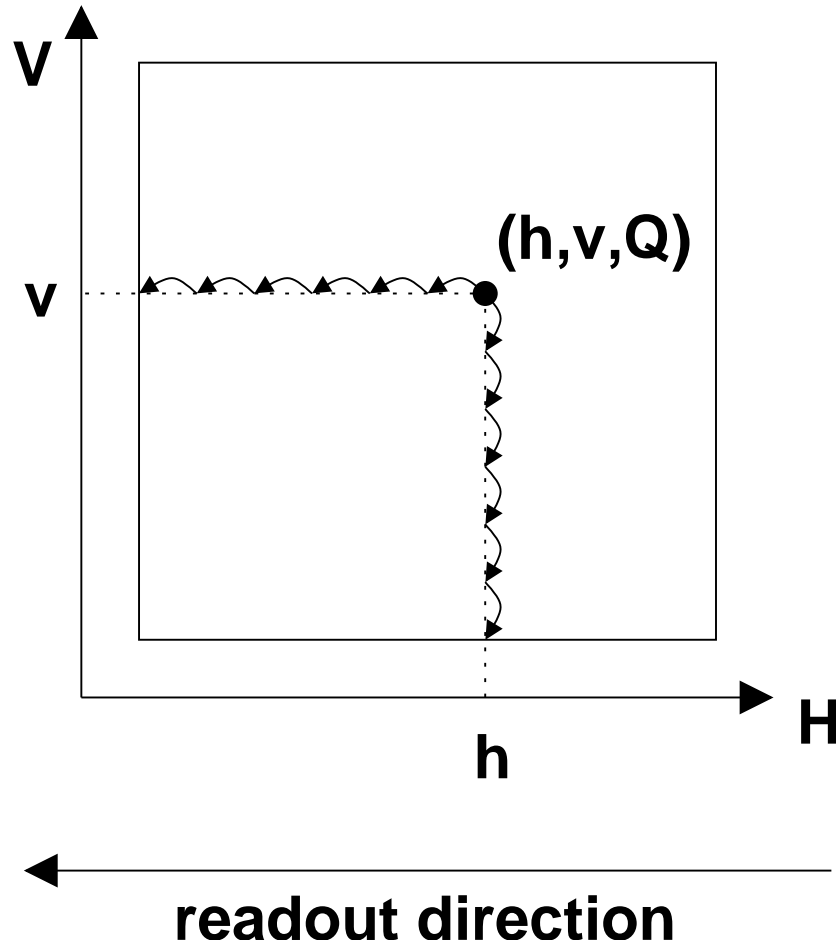
cut off outside of 3σ .

SINGLE PIXEL EVENT IV



I regard these event as single pixel event, use in analysis.

ANALYSIS METHOD I

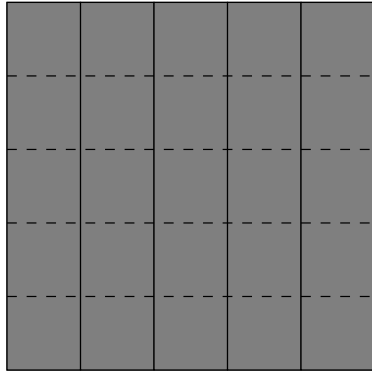


two method:

- using the least-squares method to dataset (h, v, Q) .
- divide CCD frame in five region. (talk about later)

ANALYSIS METHOD II

CCD frame



neglect HCTI effects in each region

$$Q = Q_0 \epsilon^V (\epsilon : \text{VCTE})$$

$$Q = \ln \epsilon V + \ln Q_0$$

plot dataset($v, \ln Q$), and fit.

$$y = p_1 x + p_0$$

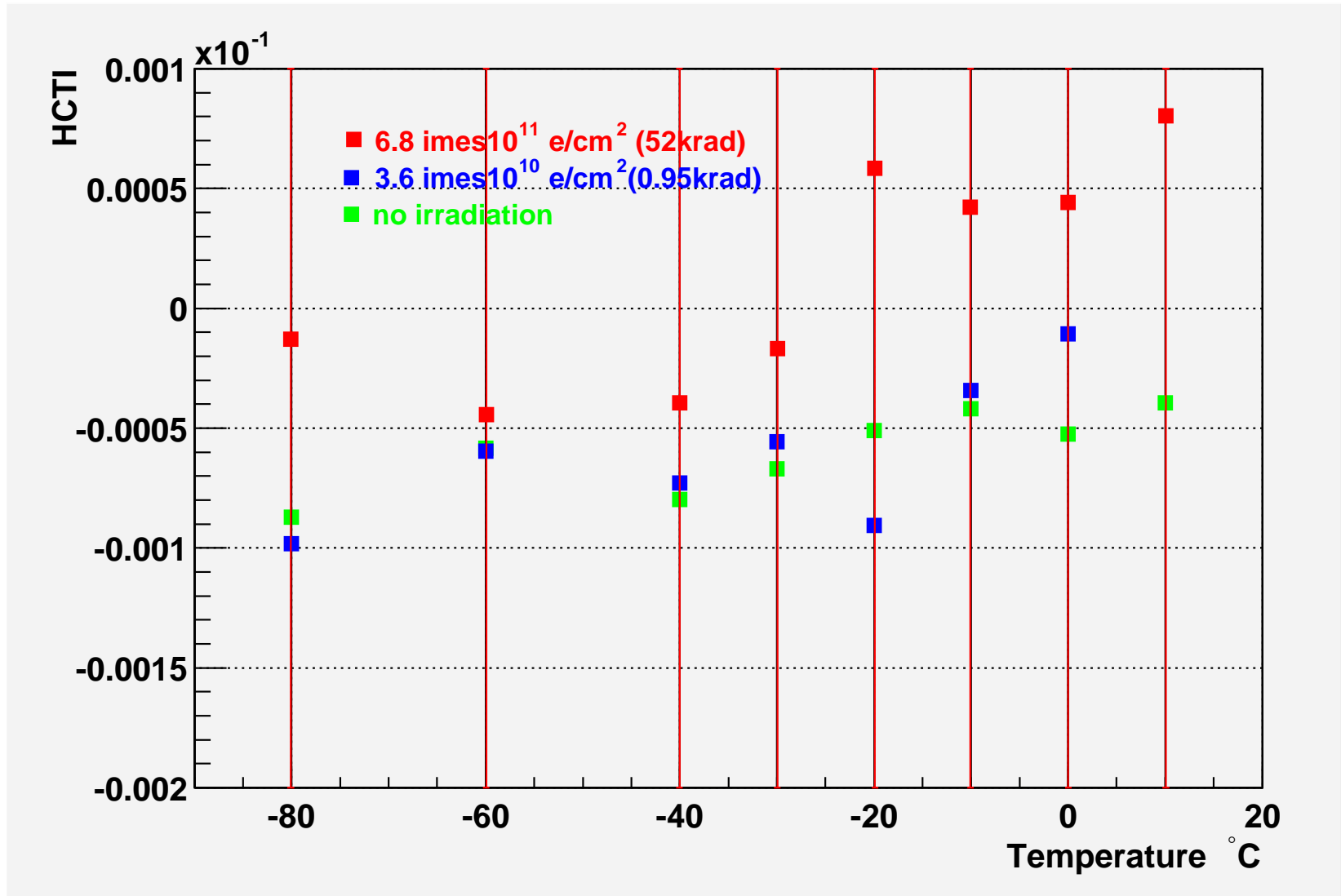
$$\ln \epsilon = p_1$$

$$\text{VCTI} = 1 - e^{p_1}$$

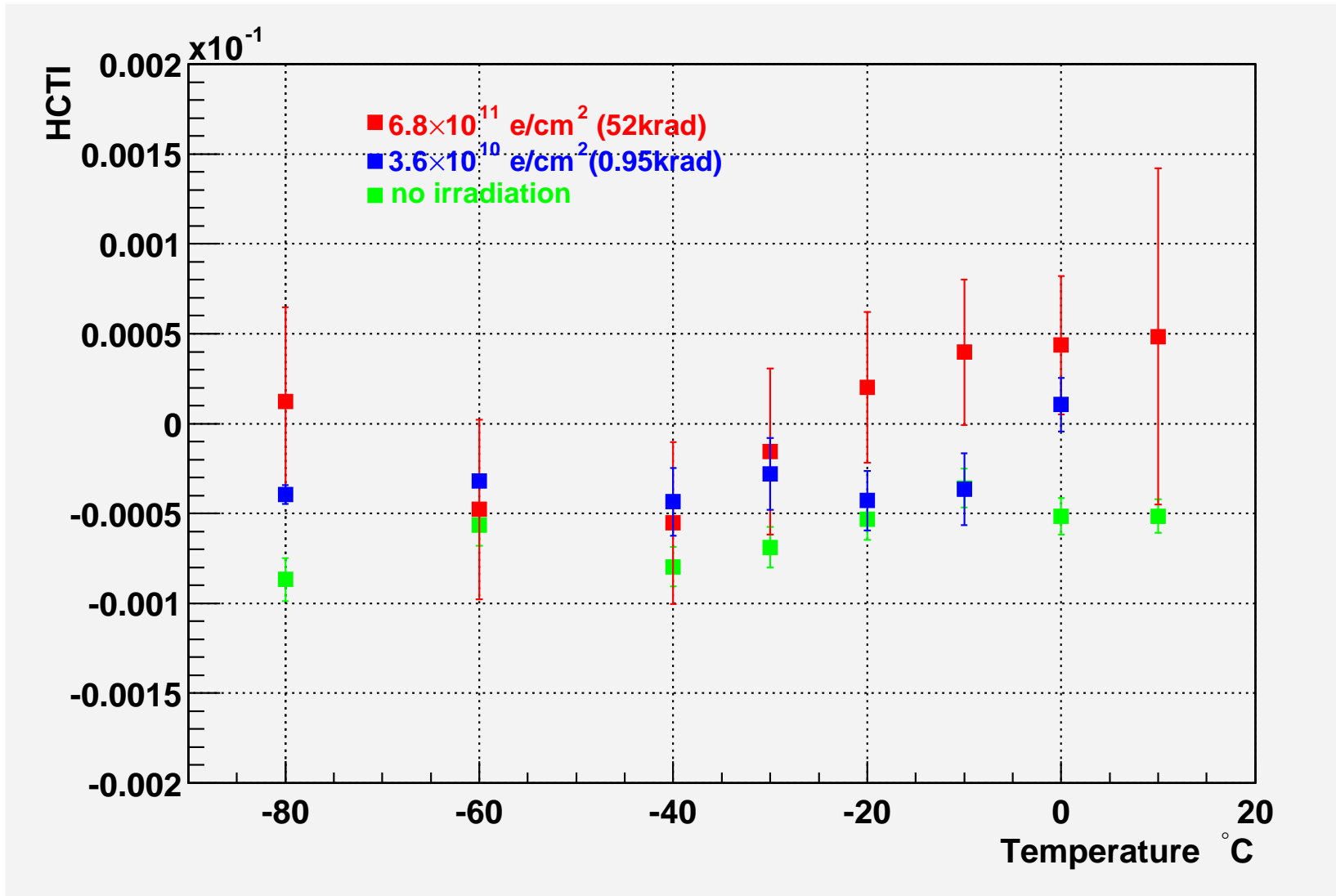
MEASURING POINT

- no irradiated CCD for reference
- irradiated CCD by ^{90}Sr
 $6.8 \times 10^{11} e/\text{cm}^2$ (52 krad)
- irradiated CCD by e^- BEAM($\sim 100\text{MeV}$)
 $3.6 \times 10^{10} e/\text{cm}^2$ (0.95 krad)
- -80°C , -60°C , -40°C , -30°C , -20°C , -10°C , 0°C ,
 10°C
8 points every CCDs.

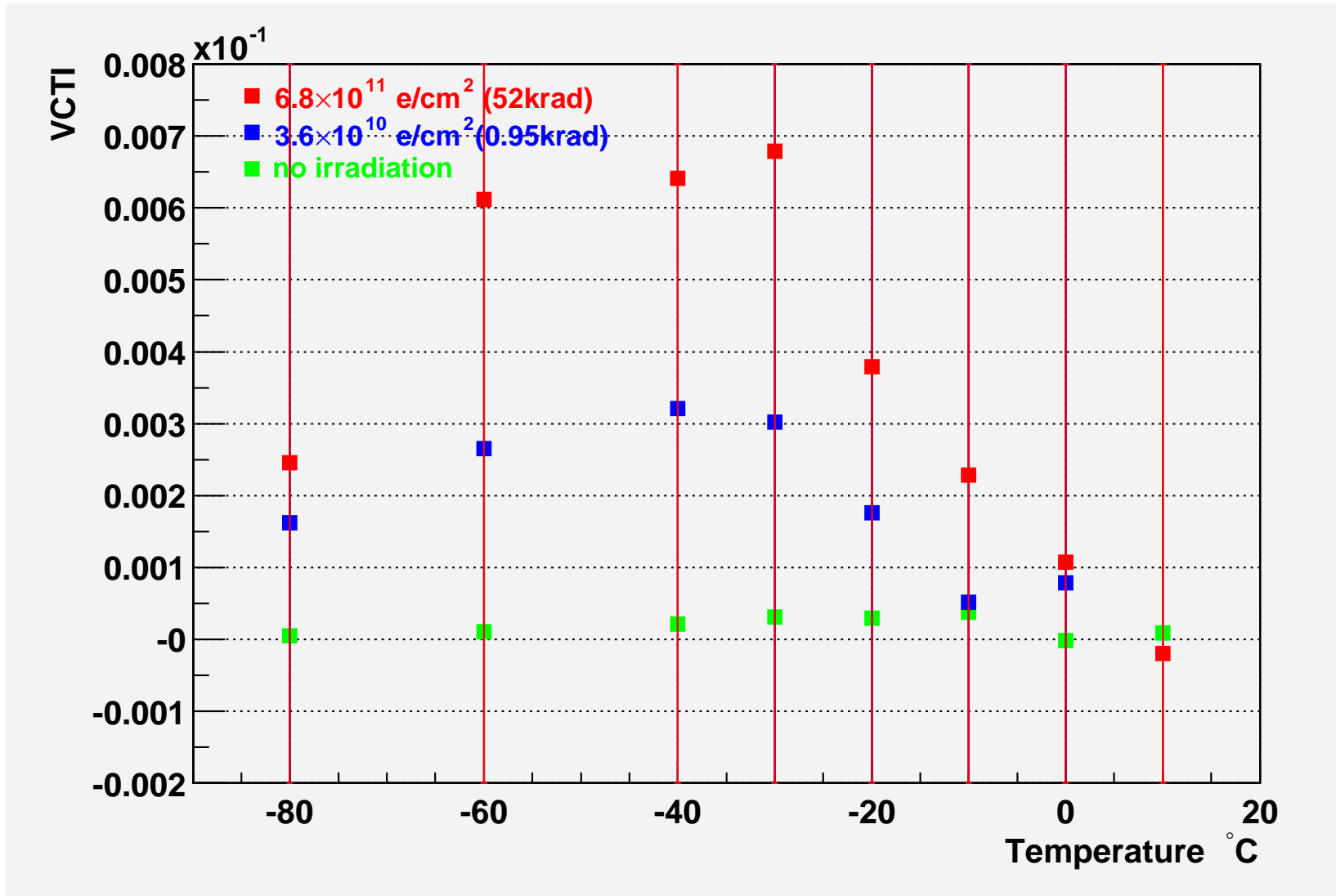
RESULT I



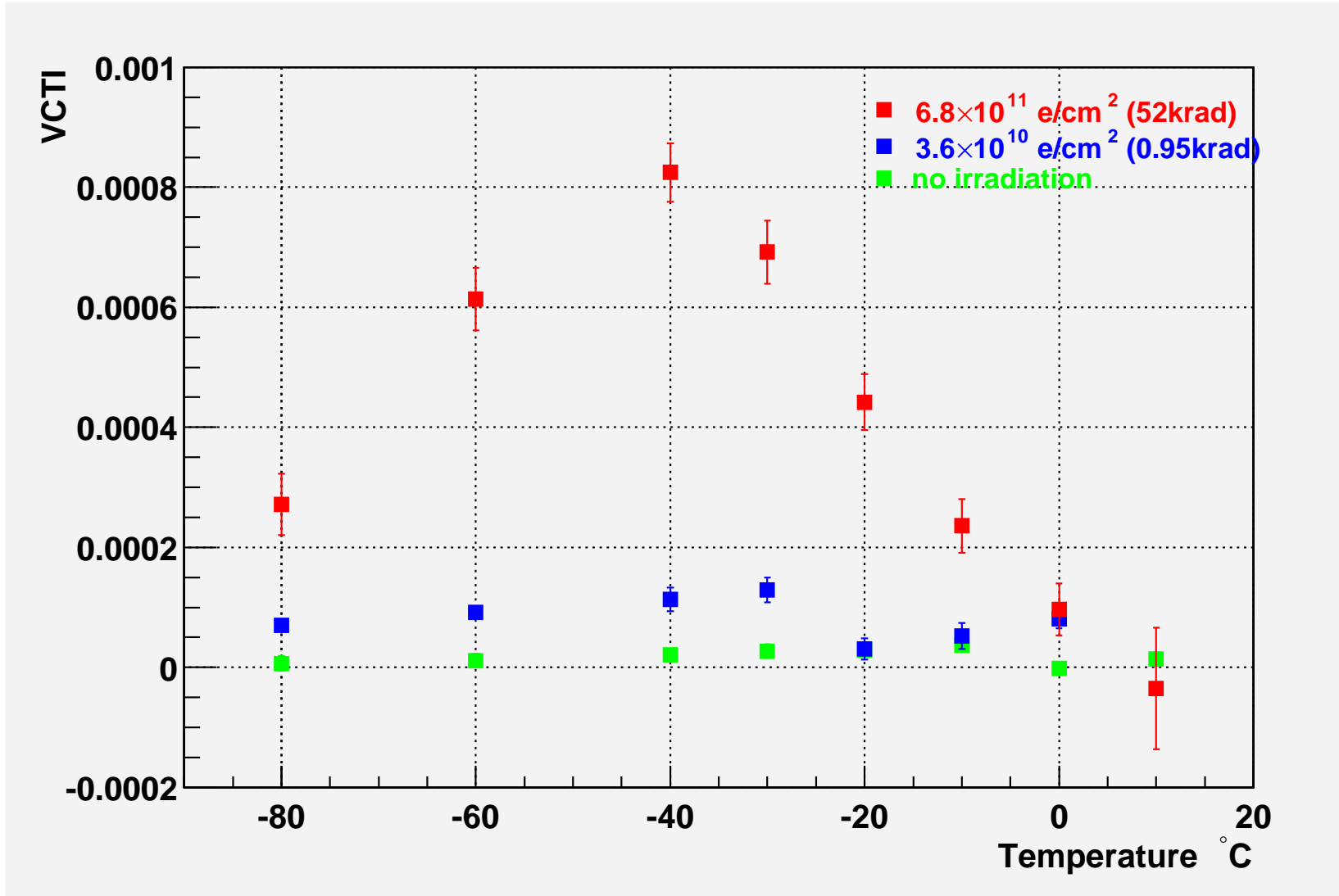
RESULT II



RESULT III



RESULT IV



SUMMARY

HCTI is very small.

0°C, VCTI $> 1.0 \times 10^{-3}$:

On the supposition that 1000(H) \times 200(V) pixel model chip, CTE is 0.67 even if worst happens.

	Method I	Method II
High energy e^-	$\sim 10^{12} e/cm^2$	$\sim 10^{12} e/cm^2$
Low energy e^-	$\sim 10^{12} e/cm^2$	$\sim 10^{12} e/cm^2$

contains 1 year at JLC beam background.